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Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



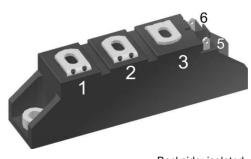
Thyristor Module

MCC21-12io8B

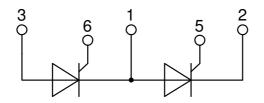
V_{RRM}	<i>=</i> 2x 1200 V			
I _{tav}	=	21 A		
VT	=	1.52 V		

Phase leg

Part number MCC21-12io8B



Backside: isolated **E**72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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MCC21-12io8B

Thyristo	r			1	Ratings	5	1
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM/DSM}	max. non-repetitive reverse/forwa	ard blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
V _{RRM/DRM}	max. repetitive reverse/forward b	locking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
R/D	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{VJ} = 25^{\circ}C$			100	μA
		$V_{R/D} = 1200 V$	$T_{VJ} = 125^{\circ}C$			5	mA
V _T	forward voltage drop	$I_{T} = 45 \text{ A}$	$T_{VJ} = 25^{\circ}C$			1.45	V
		$I_{T} = 90 \text{ A}$				1.89	V
		$I_{T} = 45 \text{ A}$	T _{vJ} = 125°C			1.52	V
		Ι _τ = 90 A				2.20	V
I TAV	average forward current	$T_c = 85^{\circ}C$	T _{vJ} = 125°C			21	A
I T(RMS)	RMS forward current	180° sine				33	A
V _{T0}	threshold voltage		T _{v.i} = 125°C			0.85	V
r _T	slope resistance } for power l	oss calculation only	10			15	mΩ
R _{thJC}	thermal resistance junction to cas	Se .				1.1	K/W
R _{thCH}	thermal resistance case to heatsi				0.20		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$		0.20	90	W
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VI} = 45^{\circ}C$			320	A
ISM		t = 8,3 ms; (60 Hz), sine	$V_{\rm VJ} = 0$ V			345	A
		t = 0.0 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$T_{VJ} = 125^{\circ}C$			270	A
		t = 8,3 ms; (60 Hz), sine	$V_{\rm NJ} = 0$ V			295	A
l²t	value for fusing	t = 0.3 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			510	A ² s
1-1	value for fushing						-
		t = 8,3 ms; (60 Hz), sine	$\frac{V_{R} = 0 V}{T_{R} + 105 \Omega}$			495	A ² s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 125^{\circ}C$			365	A ² s
•	ium etian anna site a sa	t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			360	A ² s
C	junction capacitance	$V_{\rm R}$ = 400 V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		22		pF
P _{GM}	max. gate power dissipation	$t_{\rm P} = 30 \ \mu s$	$T_{c} = 125^{\circ}C$			10	W
		$t_{P} = 300 \mu s$				5	W
P _{GAV}	average gate power dissipation					0.5	W
(di/dt) _{cr}	critical rate of rise of current	$T_{vJ} = 125 ^{\circ}C; f = 50 Hz$ re				150	A/μs
		t_{P} = 200 µs; di _G /dt = 0.45 A/µs; -					1
			on-repet., $I_{T} = 21 \text{ A}$			500	A/μs
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$			1000	V/µs
		$R_{GK} = \infty$; method 1 (linear volta	age rise)				
V _{gt}	gate trigger voltage	$V_{D} = 6 V$	$T_{VJ} = 25^{\circ}C$			1	V
			$T_{vJ} = -40 ^{\circ}C$			1.2	V
I _{GT}	gate trigger current	$V_{D} = 6 V$	$T_{VJ} = 25^{\circ}C$			65	mA
			$T_{VJ} = -40 ^{\circ}\text{C}$			80	mA
V _{gd}	gate non-trigger voltage	$V_{\rm D} = \frac{2}{3} V_{\rm DRM}$	T _{vJ} = 125°C			0.2	V
I _{GD}	gate non-trigger current					5	mA
	latching current	t _p = 10 μs	$T_{VJ} = 25 °C$			150	mA
-	-	$I_{\rm g} = 0.3 \text{A}; \text{di}_{\rm g}/\text{dt} = 0.3 \text{A}/\mu$					1 1 1
I _H	holding current	$V_{\rm D} = 6 \ V \ R_{\rm GK} = \infty$	$T_{\rm VJ} = 25^{\circ}\rm C$			100	mA
t _{gd}	gate controlled delay time	$V_{\rm D} = \frac{1}{2} V_{\rm DRM}$	$T_{VJ} = 25^{\circ}C$			2	μs
- ya	<u> </u>	$I_{\rm G} = 0.3 \text{A}; \text{di}_{\rm G}/\text{dt} = 0.3 \text{A}/\mu$				-	μΟ
t _q	turn-off time	$V_{\rm R} = 100 \text{ V}; \ \text{I}_{\rm T} = 15 \text{ A}; \ \text{V} = \frac{2}{3}$			150		116
		$v_{\rm R} = 100 v, i_{\rm T} = 10 \Lambda, v = 2$	PORM IVJ - IUU U		150		μs

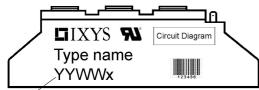
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MCC21-12io8B

Package TO-240AA					Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					200	Α
T _{vj}	virtual junction temperature				-40		125	°C
T _{op}	operation temperature				-40		100	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2.5		4	Nm
M _T	terminal torque				2.5		4	Nm
d _{Spp/App}	(App creepage distance on surface striking distance the	o Letriking dictance through air	terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}	creepage uistance on surract	e Striking distance through an	terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second			3600			V
	t = 1 minut		50/60 Hz, RMS; liso∟ ≤ 1 mA		3000			V



Date Code

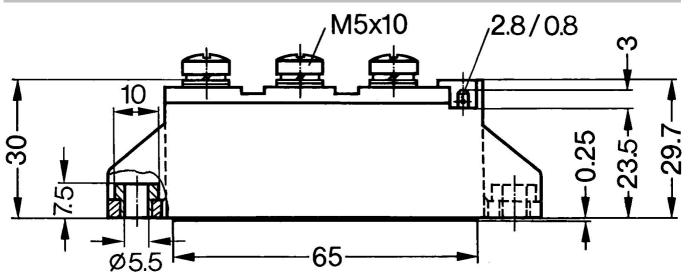
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC21-12io8B	MCC21-12io8B	Box	36	

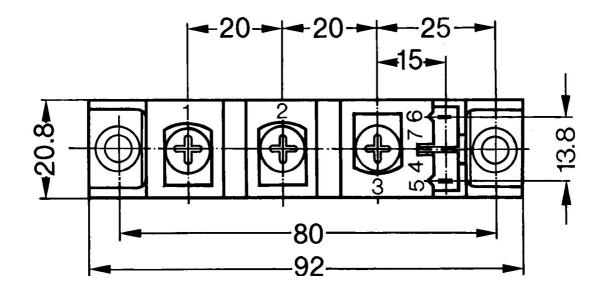
Similar Part	Package	Voltage class
MCMA25P1200TA	TO-240AA-1B	1200
MCMA35P1200TA	TO-240AA-1B	1200

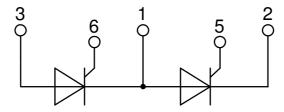
Equiva	lent Circuits for	Simulation	* on die level	T _{vj} = 125 °C
	- Ro -	Thyristor		
V _{0 max}	threshold voltage	0.85		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	13.8		mΩ

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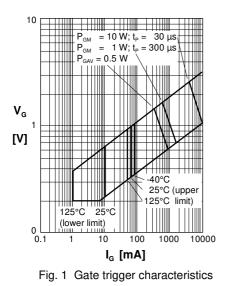
Outlines TO-240AA

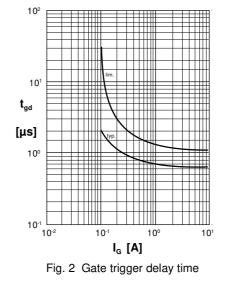






Thyristor





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